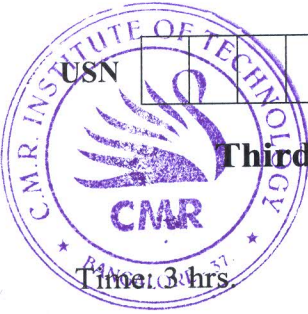


CBCS SCHEME

17EE34



Third Semester B.E. Degree Examination, June/July 2023 Analog Electronic Circuits

Max. Marks: 100

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- 1 a. Explain diode positive shunt clipper circuit with I/O waveforms and transfer characteristics. (06 Marks)
- b. With neat diagram and waveforms explain the working of a negative clamper. (06 Marks)
- c. For the clipper circuit shown in the Fig.Q.1(c), the input is $V_i = 50 \sin \omega t$. Plot the o/p voltage waveform and transfer characteristics. (08 Marks)

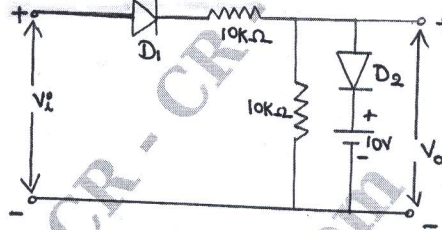


Fig.Q.1(c)

OR

- 2 a. Explain emitter bias circuit, with the help of base-emitter and collector-emitter loop. Write the necessary equations. (08 Marks)
- b. For the fixed bias circuit, derive expressions for $S_{I_{CO}}$, S_B and $S_{V_{BE}}$. (06 Marks)
- c. An emitter bias configuration has the following specifications:

$$I_{CQ} = \frac{1}{2} I_C (\text{sat}), I_C (\text{sat}) = 8\text{mA}, V_{CC} = 18\text{V} \text{ and } \beta = 110. \text{ Determine } R_B, R_C \text{ and } R_E.$$

(06 Marks)

Module-2

- 3 a. Obtain the expressions for voltage gain, input and output impedance for Emitter bias circuit with unbypassed R_E using r_e model. (10 Marks)
- b. For the network shown in Fig.Q.3(b), determine i) Z_i ii) Z_o iii) A_v iv) A_i . (10 Marks)

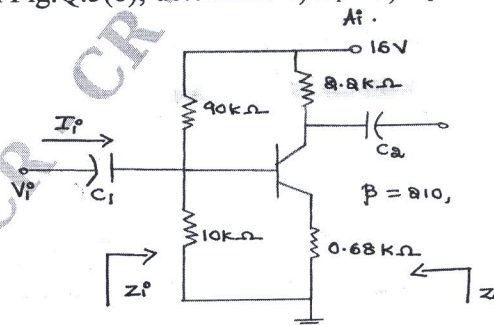


Fig.Q.3(b)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

OR

- 4 a. Derive an expression for Z_i , Z_o , A_v and A_i for voltage divider bias configuration using approximate hybrid model. (10 Marks)
- b. A transistor in CE mode has h-parameters; $h_{ie} = 1100\Omega$, $h_{re} = 2.5 \times 10^{-4}$, $h_{fe} = 100$, $h_{oe} = 25\mu A/v$. Determine the equivalent CB parameters. (04 Marks)
- c. A voltage divider bias circuit has $R_1 = 47K\Omega$, $R_2 = 10K\Omega$, $R_C = 2.2K\Omega$, $R_E = 560\Omega$, $V_{CC} = 14V$. Assuming R_E is bypassed, determine voltage gain, i/p and o/p impedance. Take h-parameters of the transistor to be $h_{ie} = 1100\Omega$, $h_{fe} = 100$, $h_{oe} = 25\mu A/v$. (06 Marks)

Module-3

- 5 a. For the cascaded arrangement shown below in Fig.Q.5(a) determine:
 - i) The loaded gain for each stage.
 - ii) The total gain for the system A_v and A_{vs}
 - iii) The total current gain for the system
 - iv) The total gain for the system if the emitter follower configuration were removed.
 - v) The phase relation between v_o and v_i . (10 Marks)

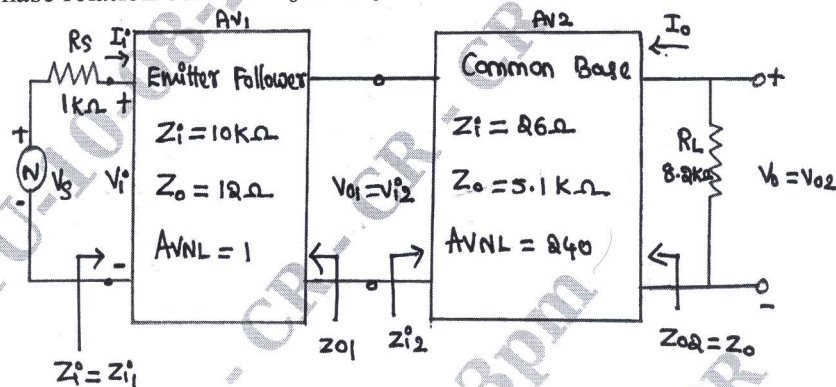


Fig.Q.5(b)

- b. Derive expression for Z_i and A_i for a Darlington, Emitter follower circuit. (10 Marks)

OR

- 6 a. With the help of block diagram, explain the concept of feedback. (08 Marks)
- b. For a current series feedback amplifier, derive an expression for output impedance with feedback. (06 Marks)
- c. Determine the voltage gain, input and output resistance with feedback for voltage series feedback having $A = -100$, $R_i = 10K\Omega$, $R_o = 20K\Omega$ for feedback of i) $\beta = -0.1$ ii) $\beta = -0.5$ (06 Marks)

CMRIT LIBRARY
BANGALORE - 560 037

Module-4

- 7 a. With neat circuit and waveforms, explain the operation of a transformer coupled class A power amplifier. (10 Marks)
- b. Show that maximum efficiency of class = B push pull power amplifier circuit is 78.5%. (10 Marks)

OR

- 8 a. With a neat circuit diagram and waveform, explain the operation of RC phase shift oscillator using BJT. Write the expression for frequency of oscillation. (10 Marks)
- b. With a neat circuit diagram and waveform, explain the working principle of crystal oscillator operating in series resonant mode. A crystal has $L = 0.334H$, $C = 0.065pF$ and $R = 5.5K\Omega$. Calculate its series resonant frequency. (10 Marks)

Module-5

- 9 a. List out the differences between BJT and FET. (05 Marks)
b. With the help of neat diagrams, explain the construction, working and characteristics of n-channel JFET. (10 Marks)
c. Obtain the expression for transconductance ' g_m ' of JFET. (05 Marks)

CMRIT LIBRARY
BANGALORE - 560 037

OR

- 10 a. With a neat sketch, explain the construction and working principle of N-channel enhancement type MOSFET and also explain its static drain characteristics. (10 Marks)
b. Determine Z_i , Z_o and A_v for JFET common source amplifier with fixed bias configuration using AC equivalent small signal model. (10 Marks)

* * * * *